

General Purpose NPN Epitaxial Planar Transistor

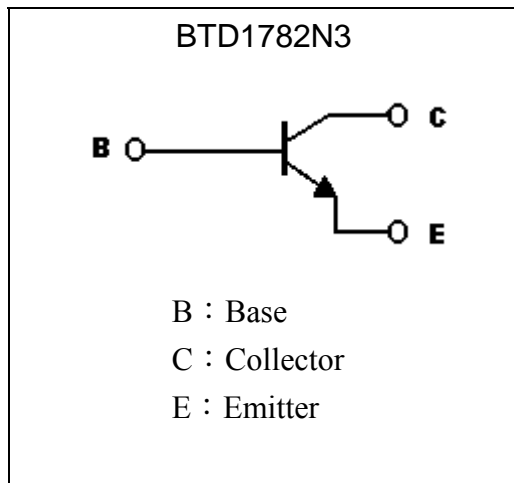
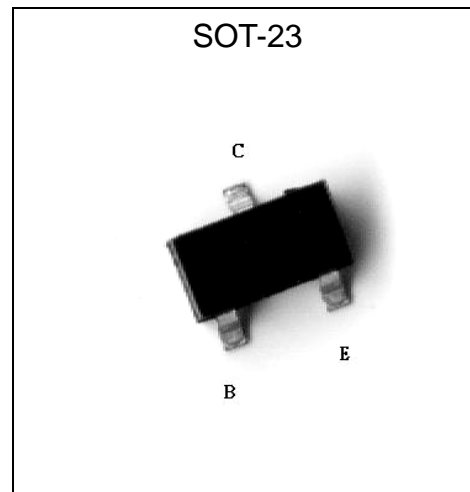
BTD1782N3

Description

The BTD1782N3 is designed for use in driver and output stages of AF amplifier and general purpose application.

Features

- Low $V_{CE(SAT)}$, $V_{CE(SAT)} = 0.15V(\text{typ}) @ I_C = 500mA / I_B = 50mA$
- High breakdown voltage, $V_{CEO} = 80V$ (min.)
- Complements to BTB1198N3
- Pb-free package

Symbol

Outline

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CB0}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current (DC)	I_C	0.5	A
Power Dissipation	P_D	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$

Note : Pulse test, $P_w \leq 10\text{ms}$, Duty $\leq 50\%$.



Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	80	-	-	V	I _C =50μA
BV _{CEO}	80	-	-	V	I _C =2mA
BV _{EBO}	5	-	-	V	I _E =50μA
I _{CBO}	-	-	0.5	μA	V _{CB} =50V, I _E =0
I _{EBO}	-	-	0.5	μA	V _{EB} =4V, I _C =0
*V _{CE(SAT)}	-	0.15	0.5	V	I _C =500mA, I _B =20mA
*h _{FE}	120	-	390	-	V _{CE} =3V, I _C =100mA
f _T	-	180	-	MHz	V _{CE} =10V, I _C =50mA, f=100MHz
C _{ob}	-	7.5	-	pF	V _{CB} =10V, I _E =0A, f=1MHz

*Pulse Test: Pulse Width ≤380μs, Duty Cycle ≤2%

Classification Of hFE

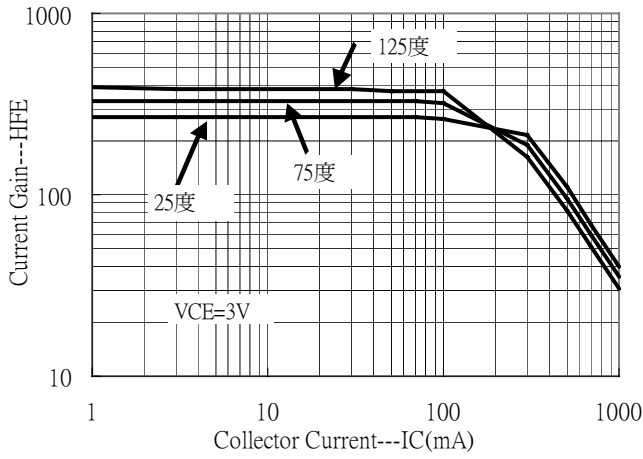
Rank	Q	R
Range	120~270	180~390

Ordering Information

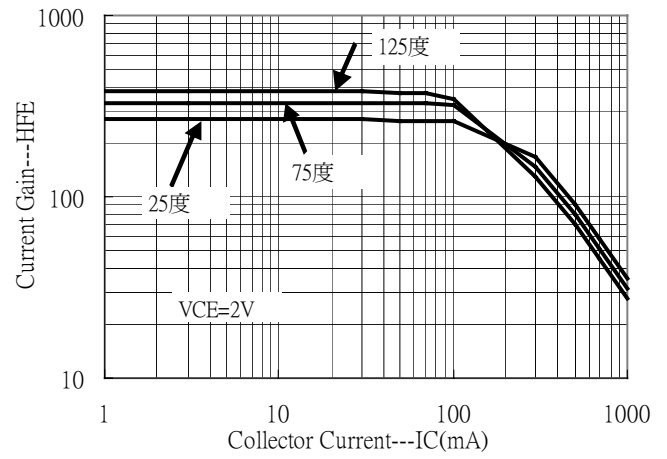
Device	Package	Shipping	Marking
BTD1782N3	SOT-23 (Pb-free)	3000 pcs / Tape & Reel	AJ

Characteristic Curves

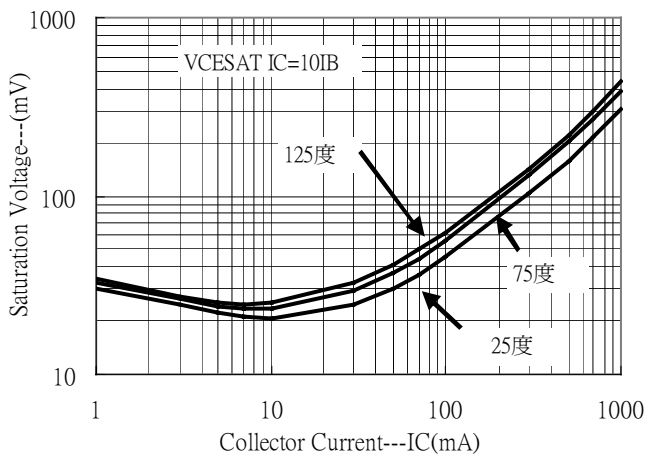
Current Gain vs Collector Current



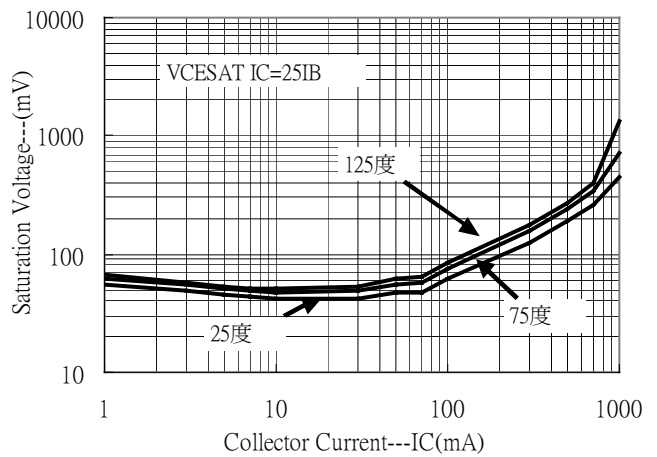
Current Gain vs Collector Current



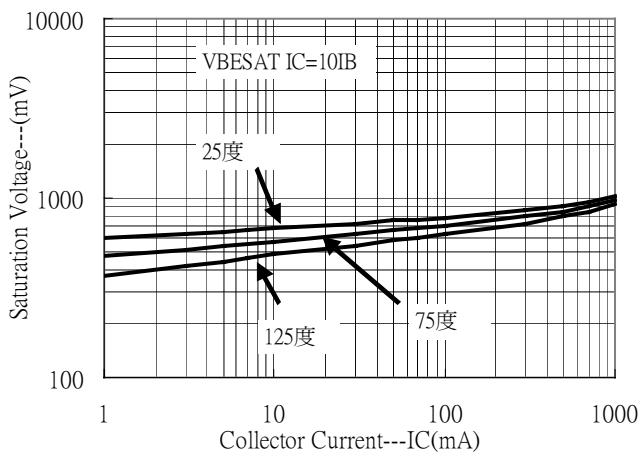
Saturation Voltage vs Collector Current



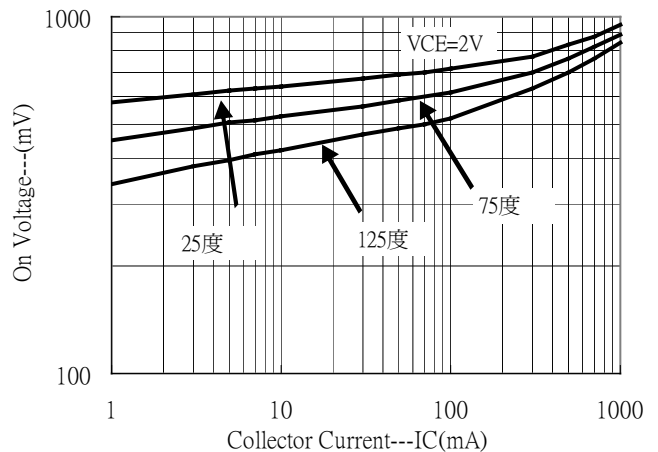
Saturation Voltage vs Collector Current



Saturation Voltage vs Collector Current

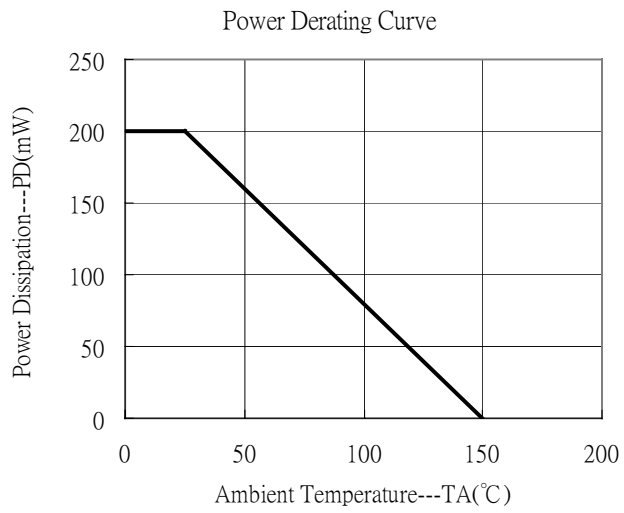


On Voltage vs Collector Current

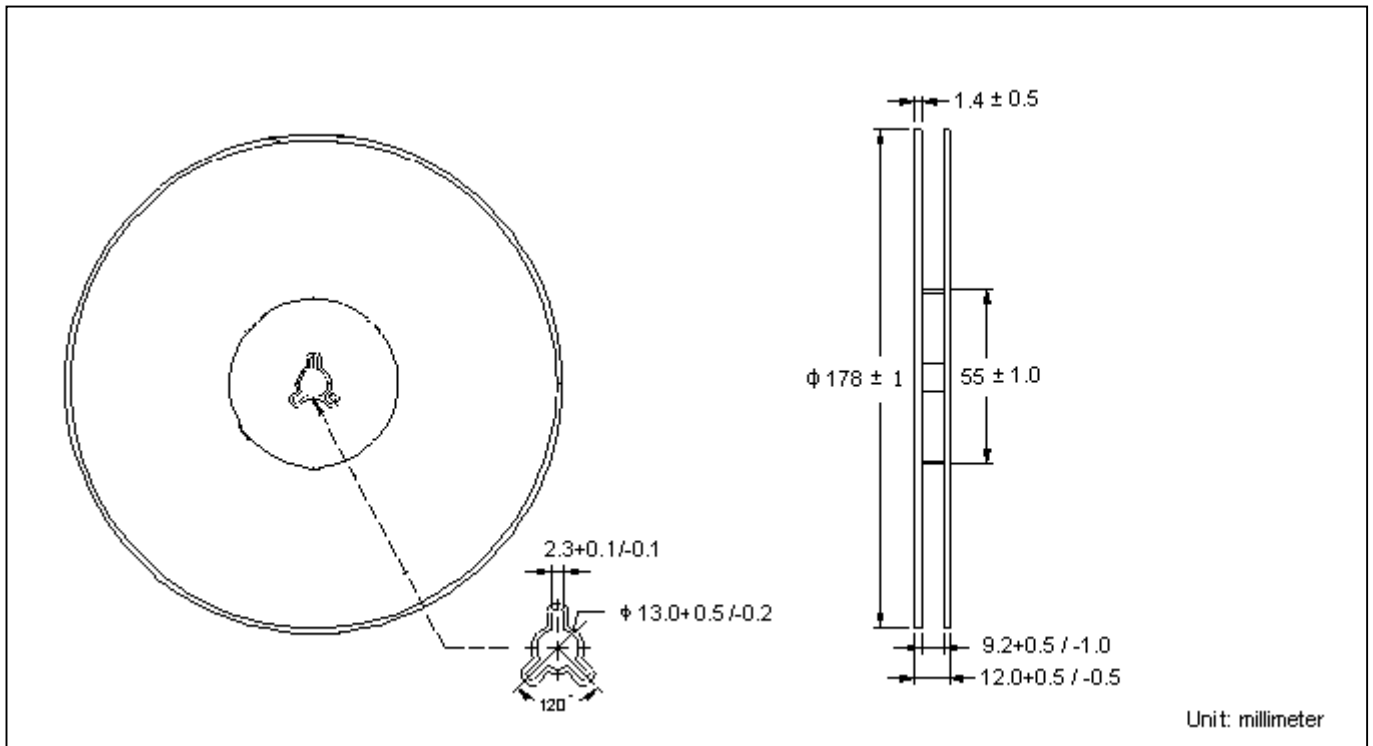




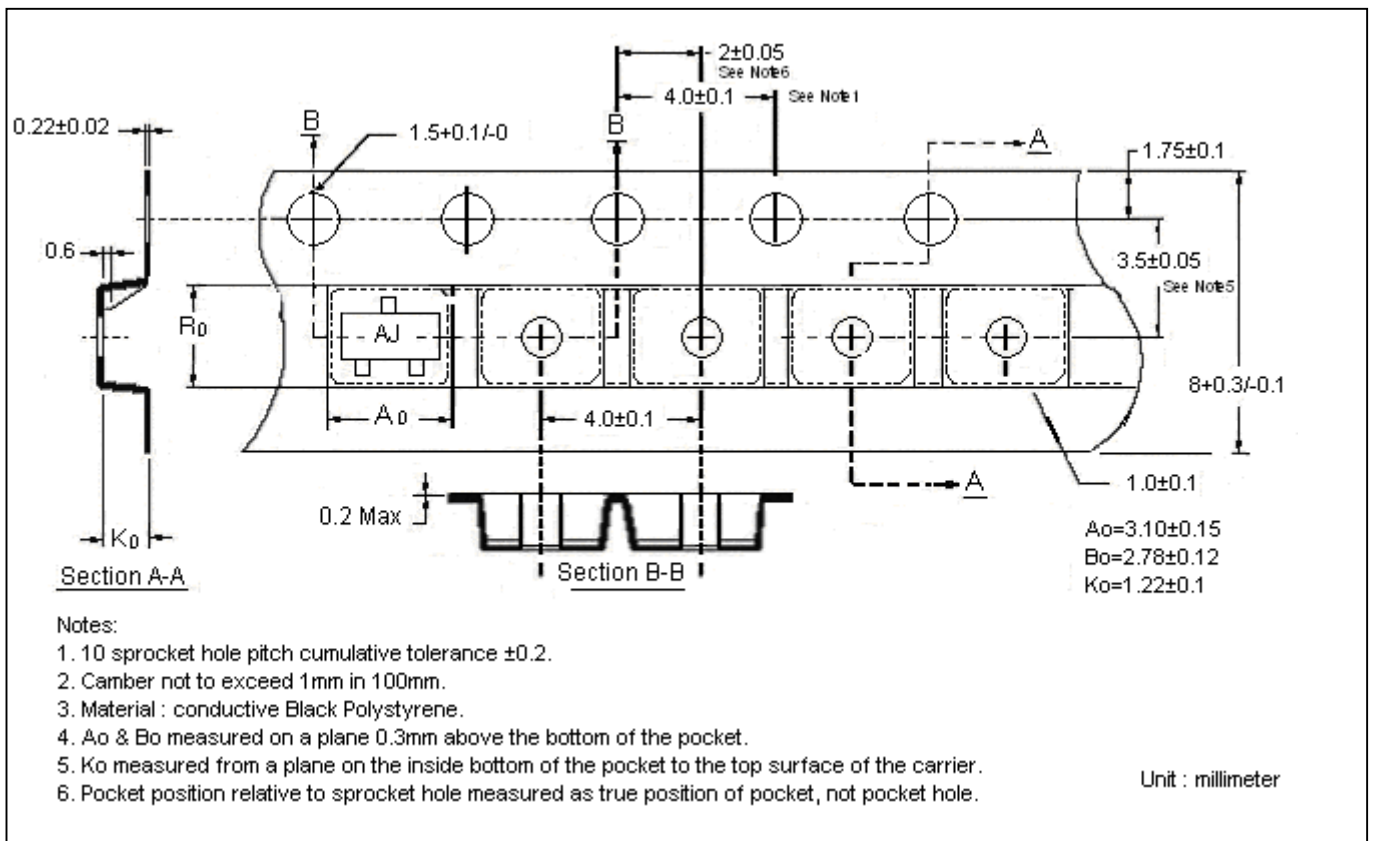
Characteristic Curves(Cont.)



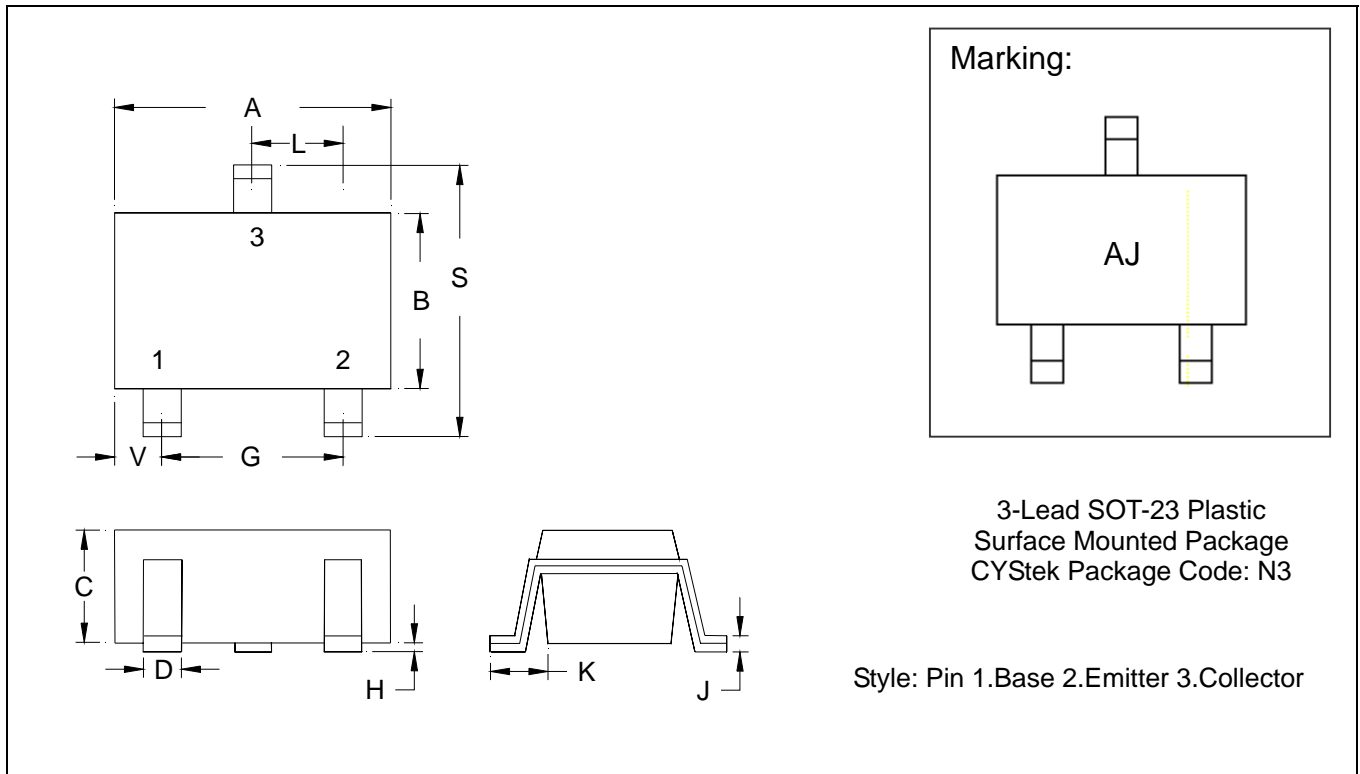
Reel Dimension



Carrier Tape Dimension



SOT-23 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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